

What is claimed is:

1. A semiconductor laser comprising:

a substrate;

5 a semiconductor lamination portion including an active layer laminated on the substrate, the semiconductor lamination portion being made of a material having a cleavage plane not parallel to a cleavage plane of the substrate; and

10 a metal layer portion provided between the substrate and the active layer in a vicinity of a resonance cavity end face.

2. The semiconductor laser according to claim 1, wherein the metal layer portion includes an element which is contained in the semiconductor lamination portion.

15 3. The semiconductor laser according to claim 1, wherein the metal layer portion is formed so as to have a width which is wider than that of a stripe-shaped portion for emitting and narrower than that of a semiconductor chip.

20 4. The semiconductor laser according to claim 1, wherein the metal layer portion is formed on a part of the semiconductor lamination portion contacted with the substrate.

5. A method for manufacturing a semiconductor laser comprising the steps of:

25 forming a semiconductor lamination portion including an active layer on a substrate, the semiconductor lamination portion being made of the material having a

cleavage plane not parallel to a cleavage plane of the substrate,

forming a metal layer portion by melting a part of the semiconductor lamination portion; and

5 forming resonance cavity end faces by cleaving the semiconductor lamination portion at the metal layer portion.

6. The method for manufacturing the semiconductor laser according to claim 5, wherein the process of forming the metal layer portion is performed by irradiating a laser
10 beam from a back surface of the substrate opposite to a surface laminated with the semiconductor lamination portion, and thereby melting a part of the semiconductor lamination portion.

7. The method for manufacturing the semiconductor
15 laser according to claim 5, wherein a wavelength of the laser beam is set longer than a wavelength corresponding to a band gap of the active layer and shorter than a wavelength corresponding to a band gap of a semiconductor layer to be melted.